

μ PA2811T1L

MOS FIELD EFFECT TRANSISTOR

R07DS0191EJ0100 Rev.1.00 Jan 11, 2011

Description

The μ PA2811T1L is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} 30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - $R_{DS(on)} = 15 \text{ m}\Omega \text{ MAX}.$ ($V_{GS} = -10 \text{ V}, I_D = -19 \text{ A}$)
- 4.5 V Gate-drive available
- Built-in gate protection diode
- Small & thin type surface mount package with heat spreader (8-pin HVSON)
- Halogen free and RoHS compliant

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2811T1L-E1-AY * ¹	Pure Sn	Tape 3000 p/reel	8-pin HVSON (3333)
μ PA2811T1L-E2-AY * ¹			typ. 0.028 g

Note: *1. Pb-free (This product does not contain Pb in external electrode.)

Absolute Maximum Ratings ($T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	∓25	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	∓19	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓76	Α
Total Power Dissipation *2	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	3.8	W
Total Power Dissipation (T _C = 25°C)	P _{T3}	52	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	−55 to +150	°C
Single Avalanche Current *3	I _{AS}	–19	Α
Single Avalanche Energy *3	E _{AS}	36	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 83.3 °C/W Channel to Case (Drain) Thermal Resistance R_{th(ch-C)} 2.4 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

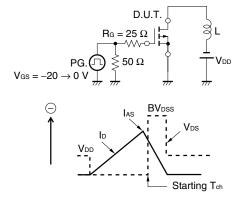
- *2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt
- *3. Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V, L = 100 μH

Electrical Characteristics ($T_A = 25^{\circ}C$)

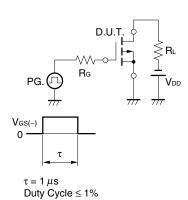
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓10	μΑ	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	7.0			S	$V_{DS} = -10 \text{ V}, I_{D} = -9.5 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		12	15	mΩ	$V_{GS} = -10 \text{ V}, I_D = -19 \text{ A}$
Resistance *1	R _{DS(on)2}		20	28	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -9.5 \text{ A}$
Input Capacitance	C _{iss}		1360		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		310		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		240		pF	f = 1 MHz
Turn-on Delay Time	$t_{d(on)}$		10		ns	$V_{DD} = -15 \text{ V}, I_D = -9.5 \text{ A},$
Rise Time	t _r		14		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	$t_{d(off)}$		100		ns	R_G = 10 Ω
Fall Time	t _f		70		ns	
Total Gate Charge	Q_G		30		nC	$V_{DD} = -24 V$,
Gate to Source Charge	Q_{GS}		5		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	Q_{GD}		10		nC	I _D = -19 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.9		V	I _F = 19 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		31		ns	I _F = 19 A, V _{GS} = 0 V,
Reverse Recovery Charge	Q _{rr}		27		nC	di/dt = 100 A/μs

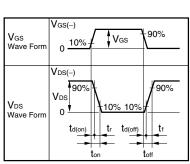
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME





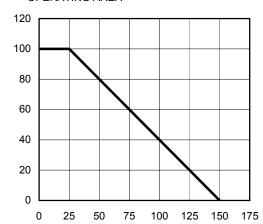
TEST CIRCUIT 3 GATE CHARGE

$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ PG. \\ \hline \\ \end{array}$$

Typical Characteristics ($T_A = 25^{\circ}C$)

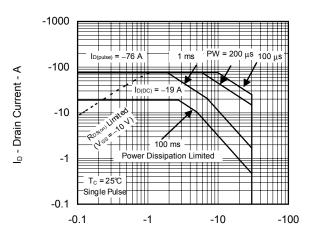
dT - Percentage of Rated Power - %

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



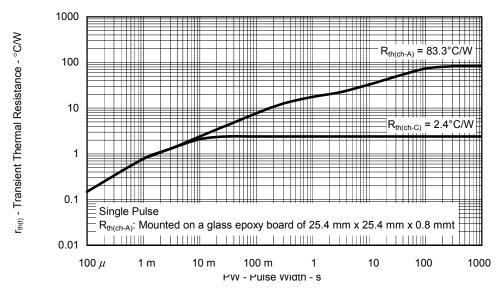
T_C - Case Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

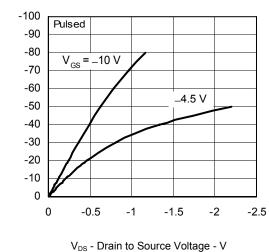


V_{DS} - Drain to Source Voltage - V

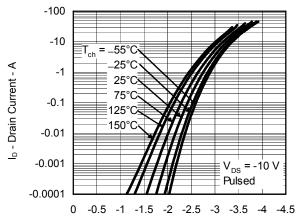
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



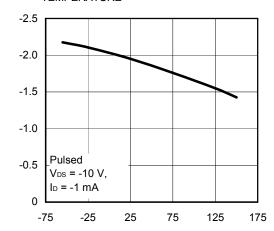
FORWARD TRANSFER CHARACTERISTICS



V_{GS} - Gate to Source Voltage - V

I_D - Drain Current - A

GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



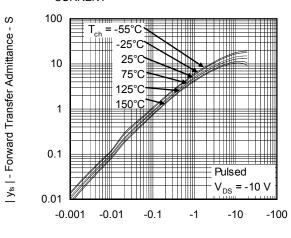
V_{GS(off)} - Gate Cut-off Voltage - V

 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

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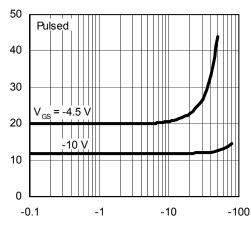
T_{ch} - Channel Temperature - °C

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



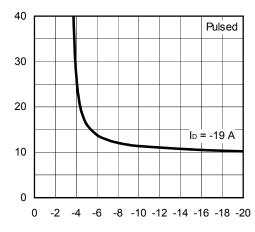
I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

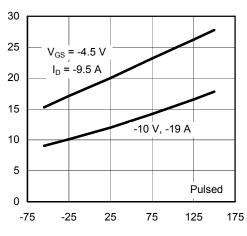


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - $m\Omega$

Coss, Crss - Capacitance - pF

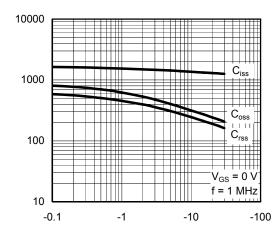
 V_{GS} - Gate to Source Voltage - V

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



 T_{ch} - Channel Temperature - $^{\circ}C$

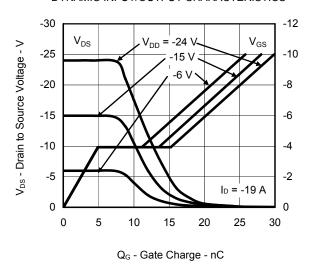
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



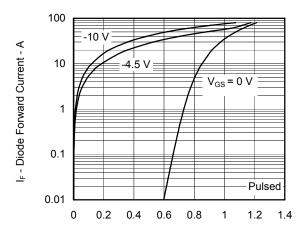
V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



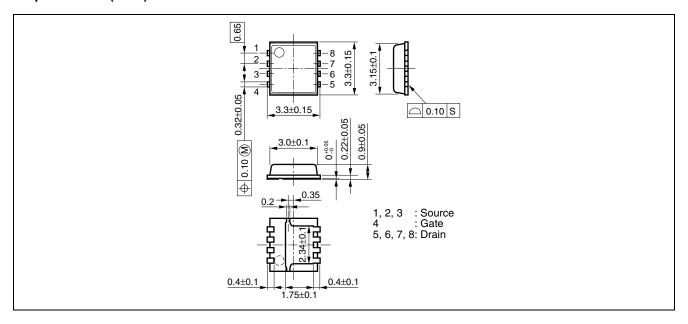
 $V_{\mbox{\scriptsize GS}}$ - Gate to Source Voltage - V



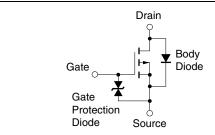
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

Package Drawings (Unit: mm)

8-pin HVSON (3333)



Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Revision History

μ PA2811T1L Data Sheet

		Description			
Rev.	Date	Page	Summary		
1.00	Jan 11, 2011	_	First Edition Issued		

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